

DH Backlighting LED in ø 3 mm Tinted Non-Diffused Package

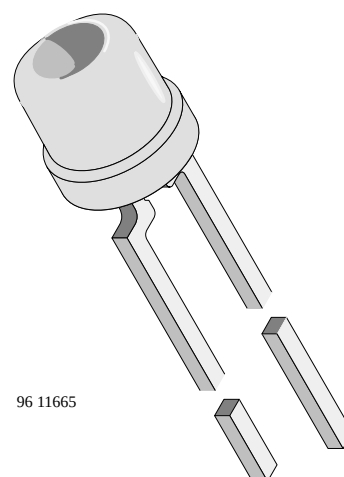
Color	Type	Technology	Angle of Half Intensity $\pm\varphi$
Double hetero red	TLVD4200	GaAlAs on GaAs	85°

Description

The TLVD4200 serie was developed for backlighting in the extrem bright double heterojunction (DH) red GaAlAs on GaAs technology. Due to its special shape the spatial distribution of the radiation is qualified for backlighting.

To optimize the brightness of backlighting a custom-built reflector (with scattering) is required. Uniform illumination can be enhanced by covering the front of the reflector with diffuser material.

This is a bright and flexible solution for backlighting different areas.



Features

- High brightness
- Wide viewing angle
- Categorized for luminous flux
- Available in DH red
- Tinted clear package
- Low power dissipation
- Low self heating
- Rugged design
- High reliability

Applications

Backlighting of display panels, LCD displays, symbols on switches, keyboards, graphic boards and measuring scales

Illumination of large areas e.g. dot matrix displays

Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

TLVD4200

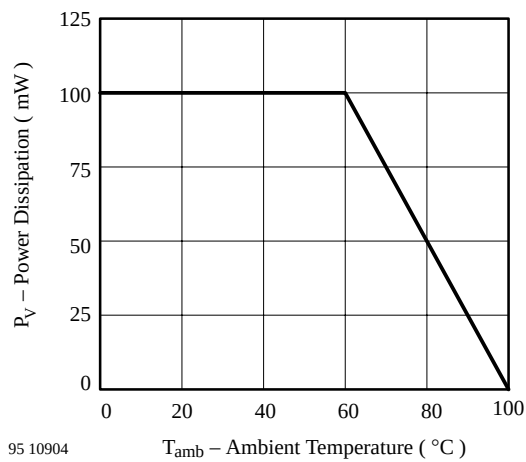
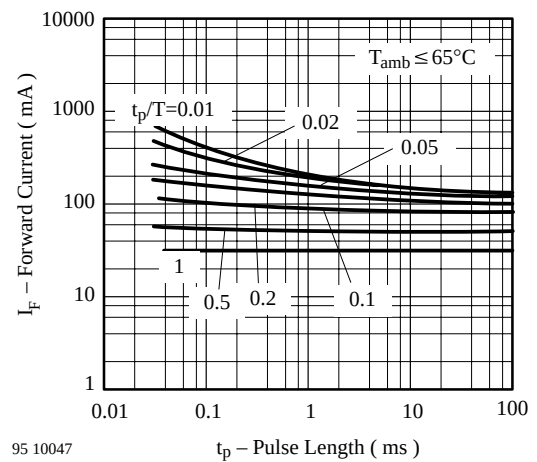
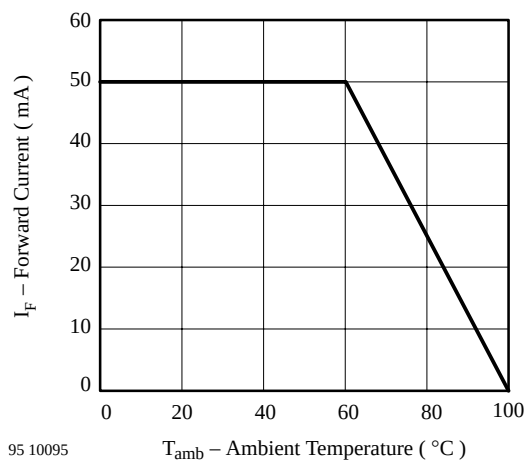
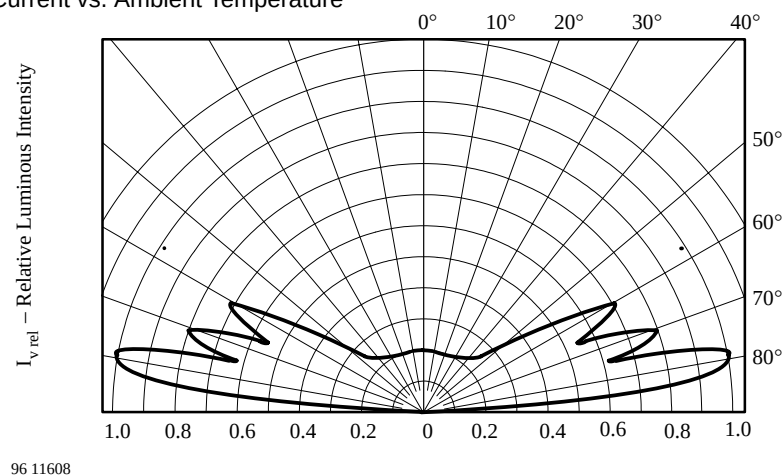
Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	6	V
DC forward current		I_F	50	mA
Surge forward current	$t_p \leq 10 \mu\text{s}$	I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 60^{\circ}\text{C}$	P_V	100	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	-20 to +100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55 to +100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5 \text{ s}$, 2 mm from body	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient		R_{thJA}	400	K/W

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Double hetero red (TLVD4200)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous flux	$I_F = 15 \text{ mA}$		ϕ_V	40	80		mlm
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d		640		nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		650		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		ϕ		± 85		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		1.8	2.2	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0$, $f = 1 \text{ MHz}$		C_j		50		pF

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

Figure 1 Power Dissipation vs. Ambient Temperature

Figure 3 Forward Current vs. Pulse Length

Figure 2 Forward Current vs. Ambient Temperature

Figure 4 Rel. Luminous Intensity vs. Angular Displacement

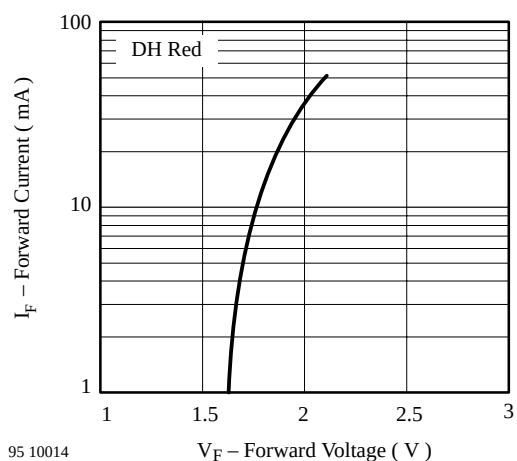


Figure 5 Forward Current vs. Forward Voltage

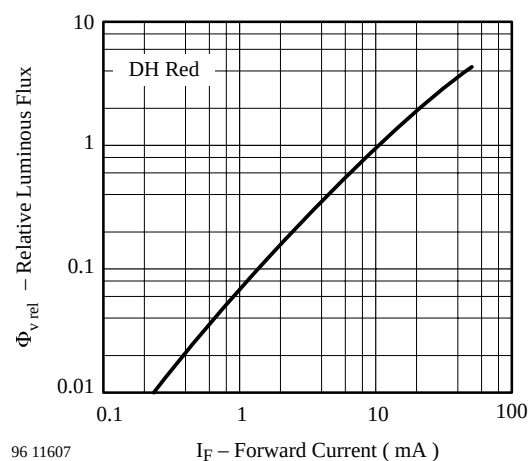


Figure 8 Relative Luminous Flux vs. Forward Current

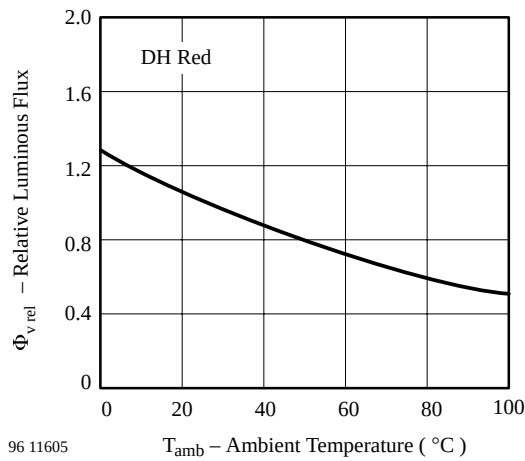


Figure 6 Rel. Luminous Flux vs. Ambient Temperature

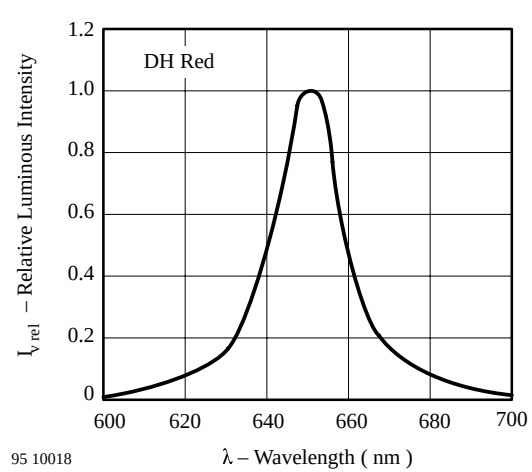


Figure 9 Relative Luminous Intensity vs. Wavelength

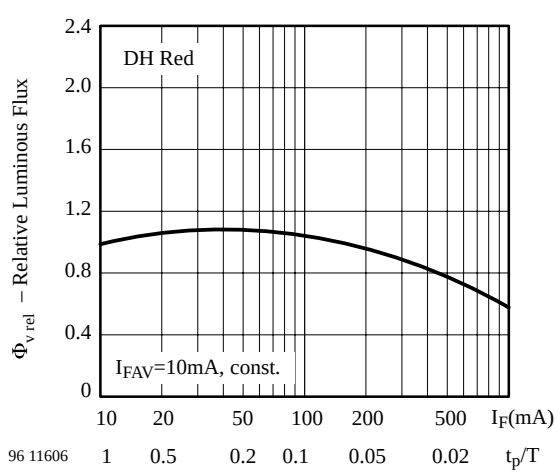
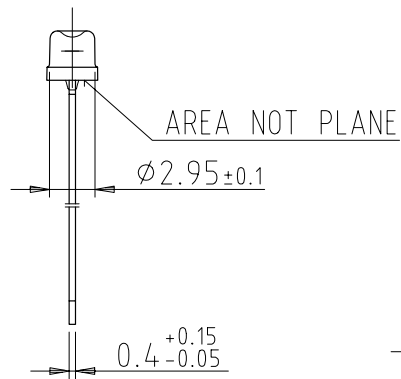
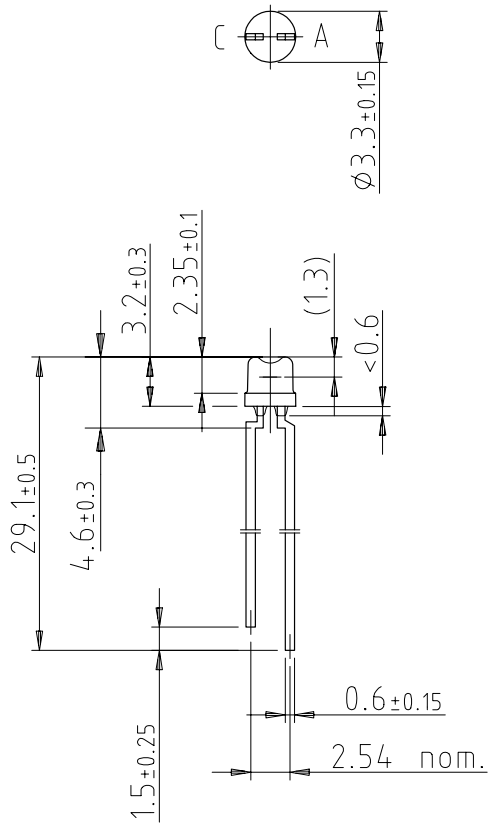


Figure 7 Rel. Luminous Flux vs. Forw. Current/Duty Cycle

Dimensions in mm



9510953

technical drawings
according to DIN
specifications

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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